

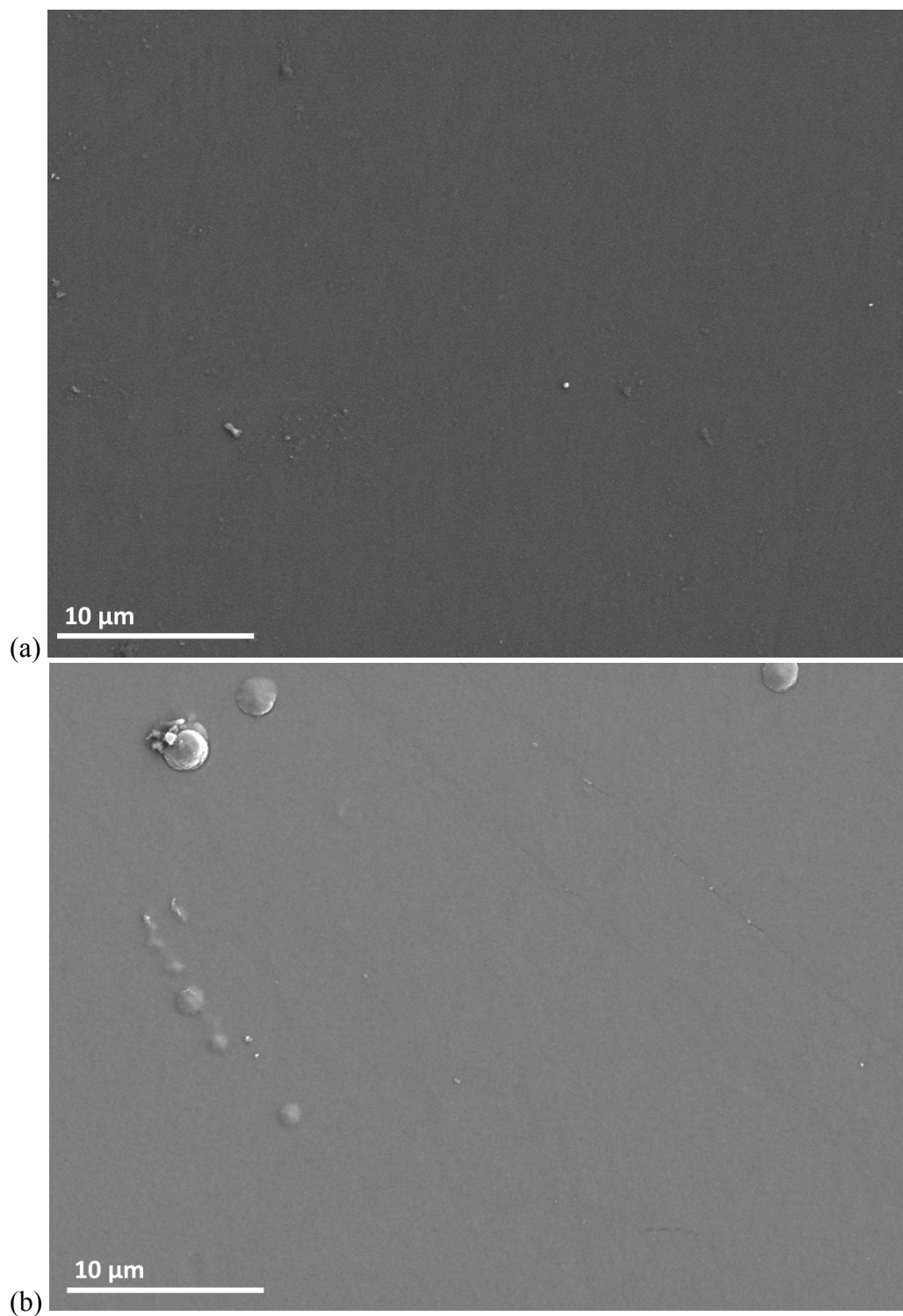
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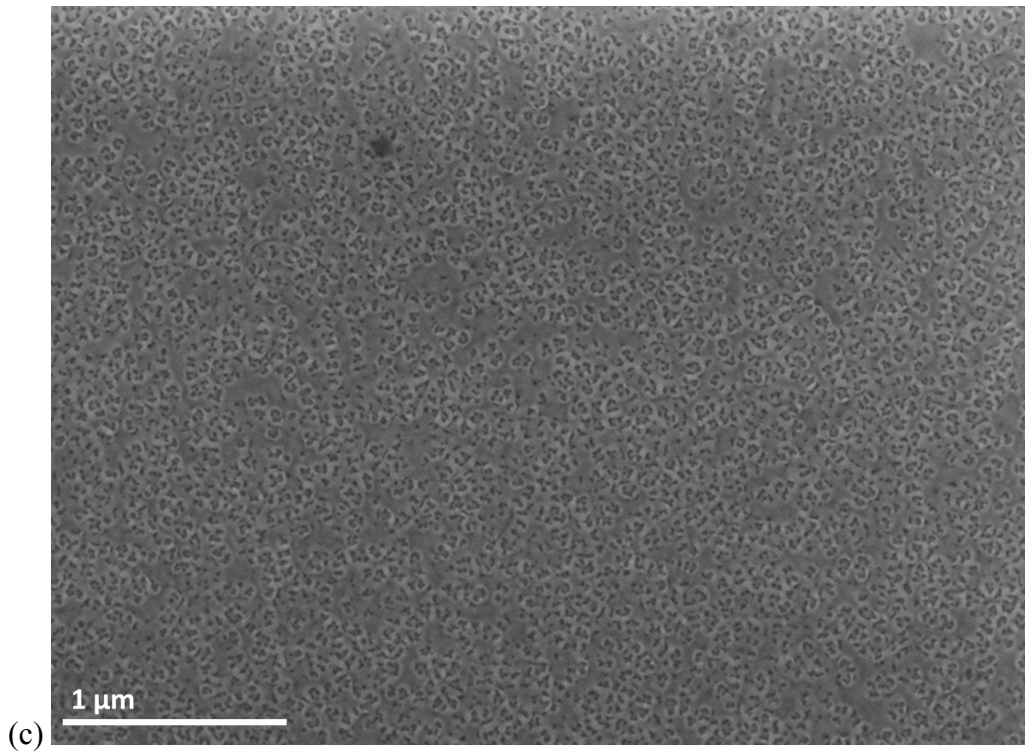
SUPPLEMENTARY INFORMATION

**Depth profiling by pulsed glow discharge time-of-flight mass spectrometry with  
combined hollow cathode cell**

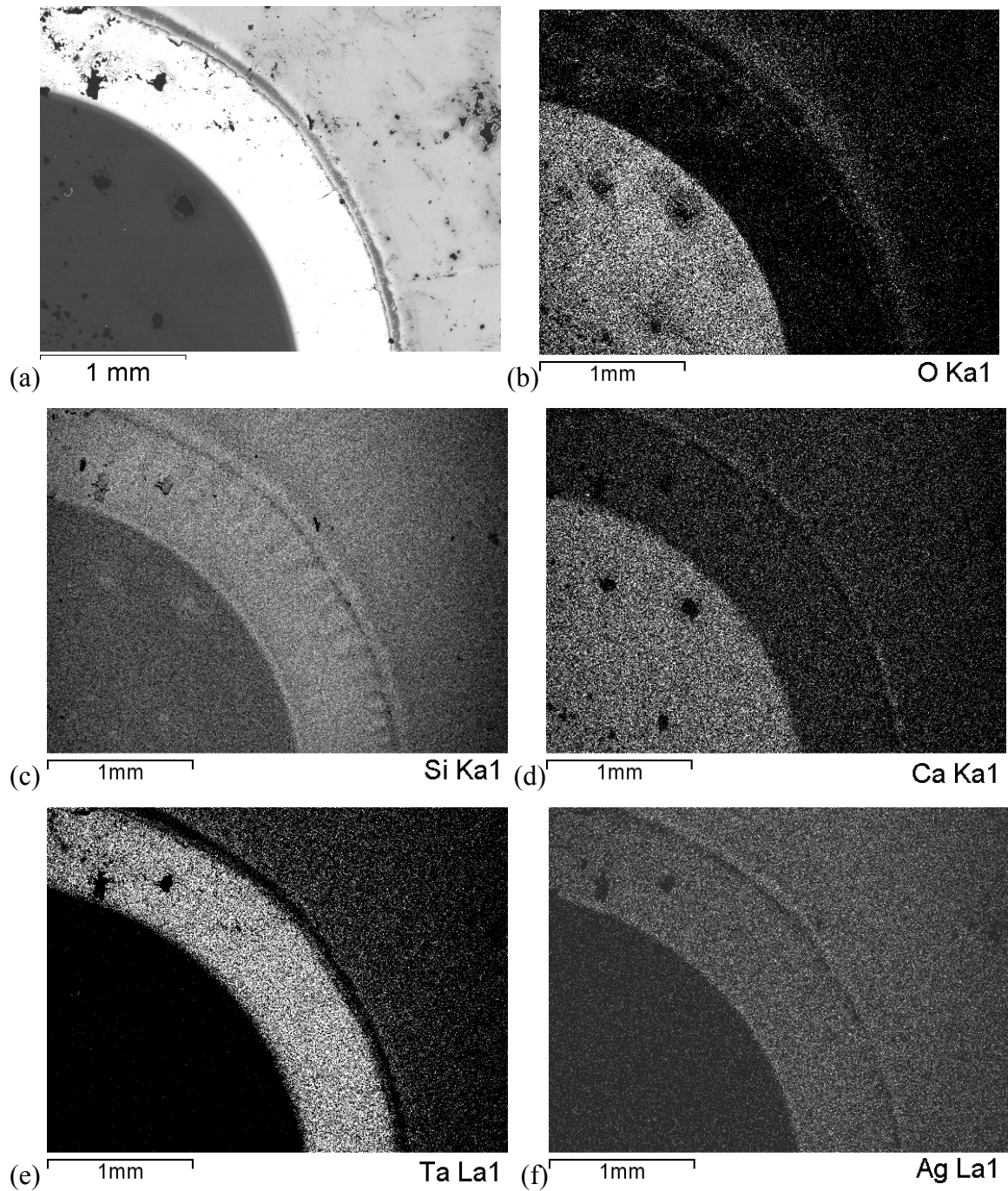
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Yakobson, Nikolay Solovyev, Alexander Ganeev

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**Fig. S1** SEM-images of Si surface in different regions of the crater after the GD sputtering in Ta CHC cell: (a) – outer part of the crater (original surface), magnification 5000X; (b) – central part of the crater's bottom, magnification 5000X; (c) – central part of the crater's bottom, magnification 50000X.



**Fig. S2** SEM EDX images of the glow discharge sputtering crater surface for the 650 nm silicon film on borosilicate glass preliminary covered with 170 nm Ta layer; auxiliary cathode made of Ta: (a) – SEM image of the part of the crater, (b), (c), (d), (e), (f) – EDX maps of the same area for O ( $K\alpha 1$ ), Si ( $K\alpha 1$ ), Ca ( $K\alpha 1$ ) (component of FIOLAX 8412 borosilicate glass), Ta ( $L\alpha 1$ ), and Ag ( $L\alpha 1$ ) emission lines, respectively.